

CMP160N10/CMB160N10/CMI160N10/CMF160N10

100V, 4mΩ typ., 160A N-Channel MOSFET

General Description

The 160N10 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

Product Summary

BVDSS	R _{DS(on)} max.	ID
100V	4.6mΩ	160A

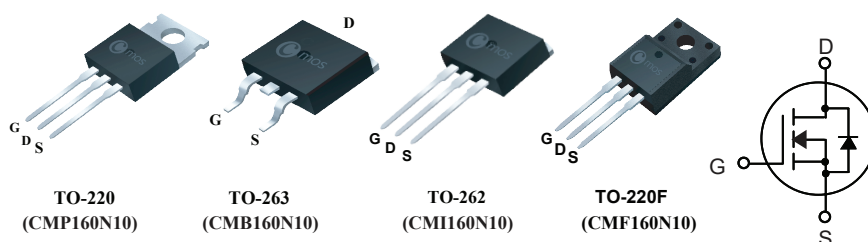
Applications

- DC to DC converters
- Synchronous Rectification

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

TO-220/263/262/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V _{DS}	Drain-Source Voltage	100		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _C =25°C	Continuous Drain Current	160	160*	A
I _D @T _C =100°C	Continuous Drain Current	110	110*	A
I _{DM}	Pulsed Drain Current	640	640*	A
EAS	Single Pulse Avalanche Energy (Note 1)	1755		mJ
P _D @T _C =25°C	Total Power Dissipation	300	60	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.(min. footprint)	48	48	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	0.42	2.08	°C/W

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Electrical Characteristics (T_J=25°C , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250μA	100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =40A	---	4	4.6	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	2	---	4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V , V _{GS} =0V	---	---	1	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =15V , I _D =15A	---	40	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	1.1	---	Ω
Q _g	Total Gate Charge	V _{DD} =50V , I _D =90A V _{GS} =10V	---	127	---	nC
Q _{gs}	Gate-Source Charge		---	46	---	
Q _{gd}	Gate-Drain Charge		---	36	---	
T _{d(on)}	Turn-On Delay Time	V _{DS} =50V , V _{GS} =10V R _{G_ext} =3Ω	---	30	---	ns
T _r	Rise Time		---	109	---	
T _{d(off)}	Turn-Off Delay Time		---	64	---	
T _f	Fall Time		---	115	---	
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz	---	8300	---	pF
C _{oss}	Output Capacitance		---	900	---	
C _{rss}	Reverse Transfer Capacitance		---	650	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Diode continuous forward current	V _G =V _D =0V , Force Current	---	---	160	A
I _{S,pulse}	Diode pulse current		---	---	640	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _F =30A , T _J =25 °C	---	0.81	1.2	V

Note :

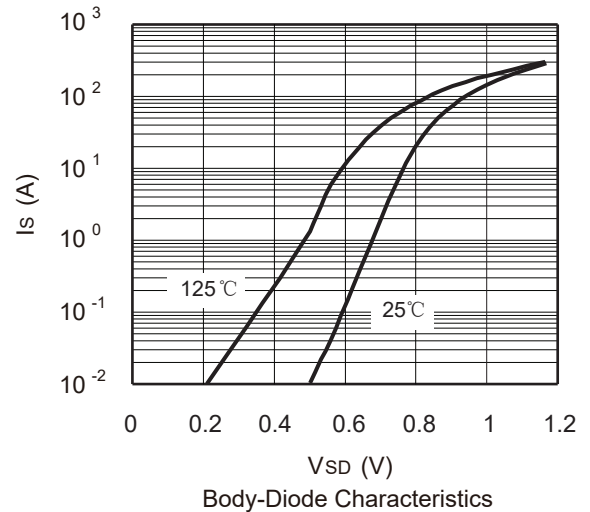
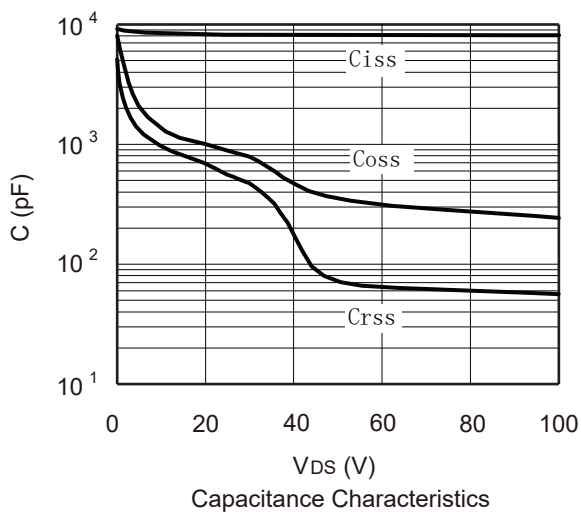
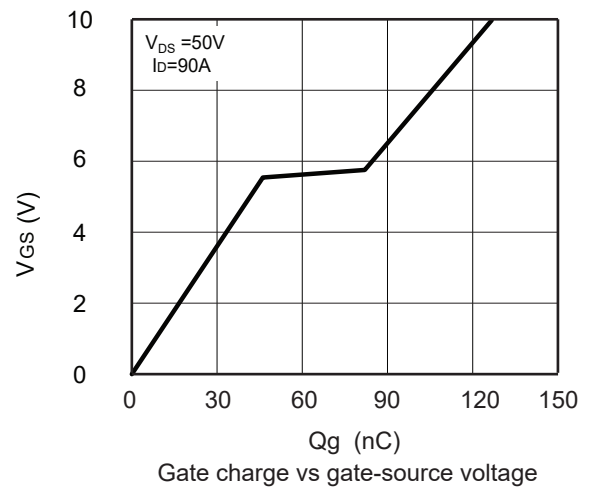
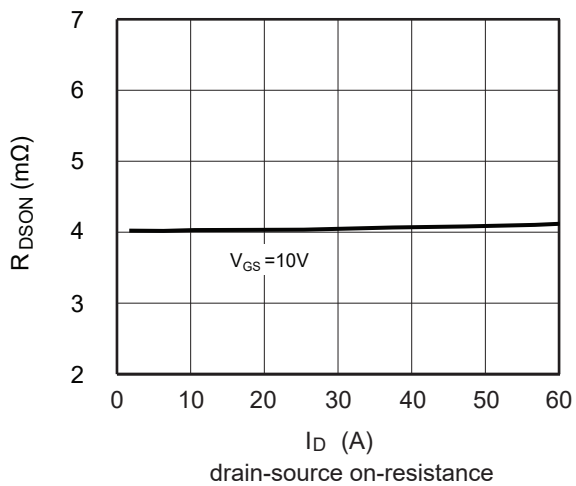
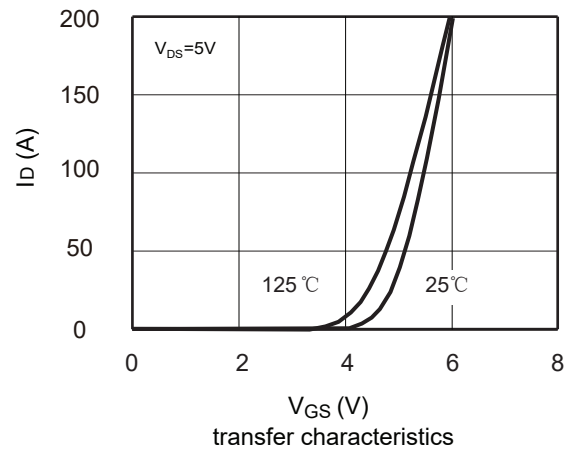
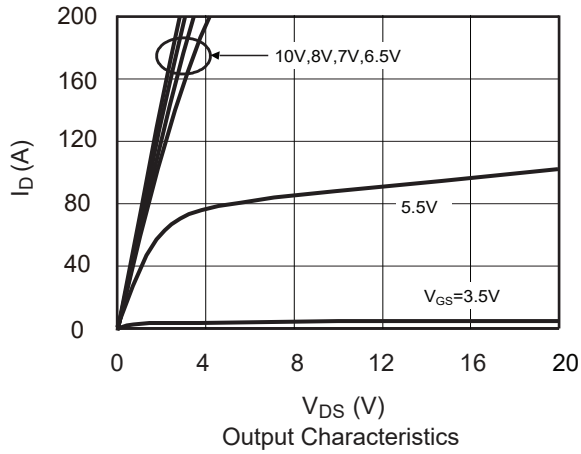
1.The EAS data shows Max. rating .The test condition is V_{DS}=50V , V_{GS}=10V , L=5mH , I_{AS}=26.5A.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

Typical Characteristics



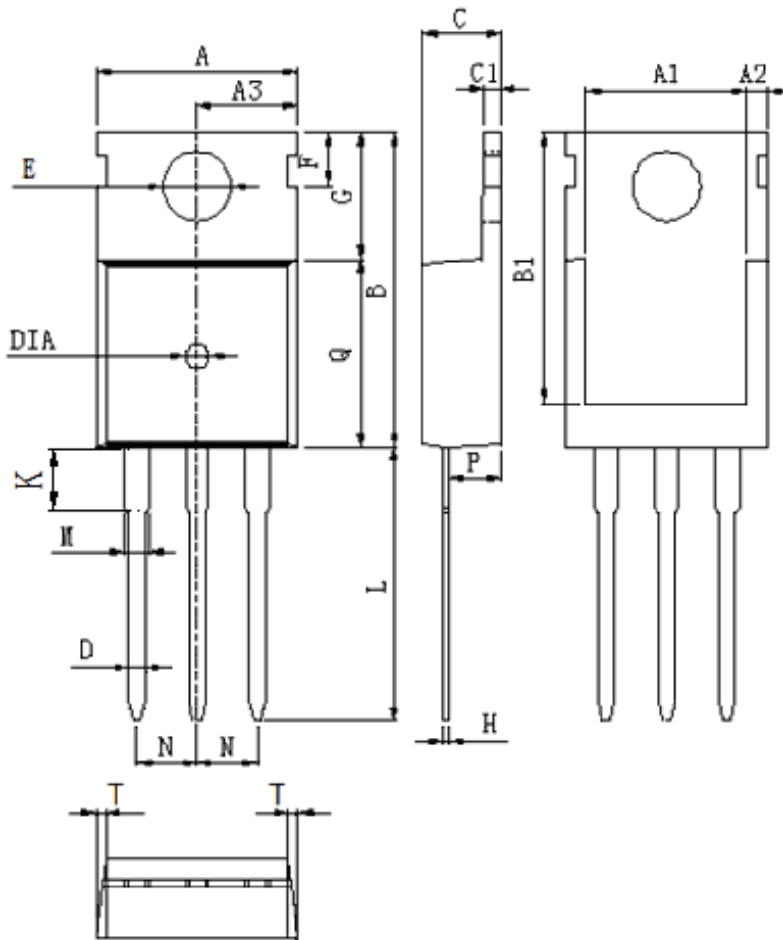
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Package Dimension

TO-220

Unit :mm



DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5 (deep 0.2)

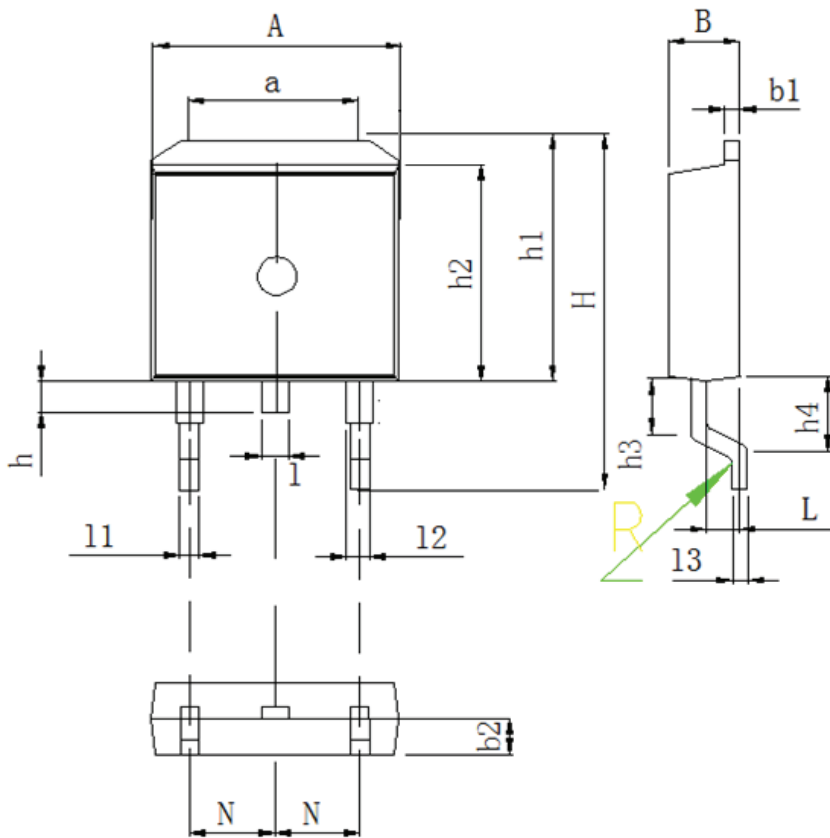
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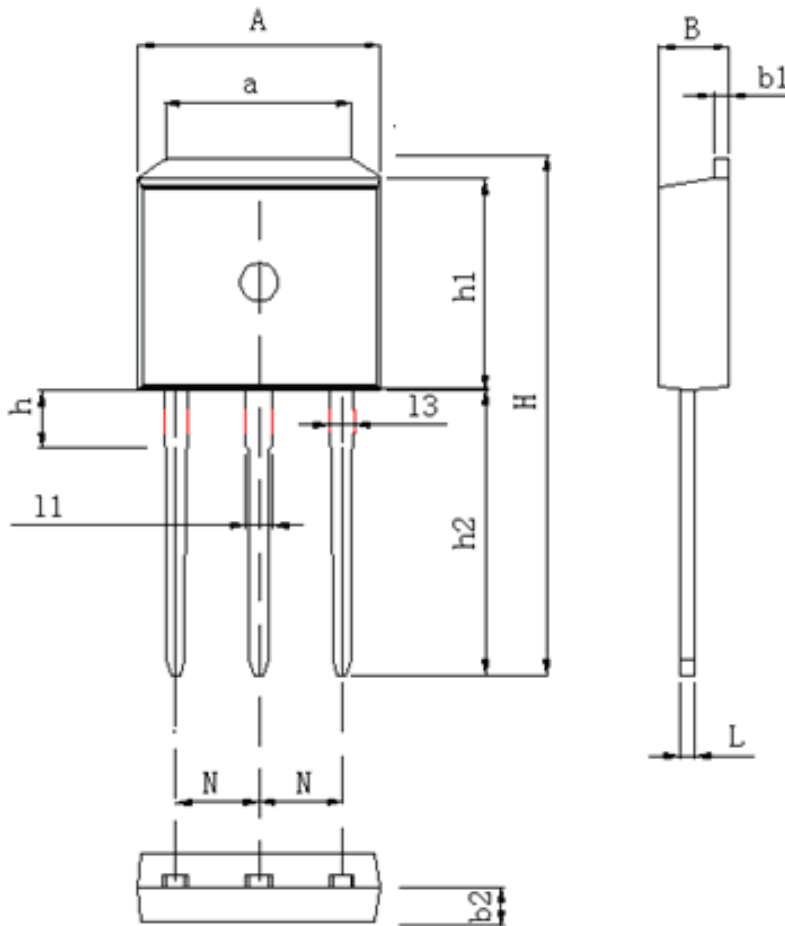
Package Dimension

TO-263

Unit :mm



DIM	MILLIMETERS
A	9.8 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	15.5 ± 0.3
h	1.54 ± 0.2
h1	10.5 ± 0.2
h2	9.2 ± 0.1
h3	1.54 ± 0.2
h4	2.7 ± 0.2
L	2.4 ± 0.2
1	1.3 ± 0.1
11	0.8 ± 0.1
12	1.3 ± 0.1
13	0.5 ± 0.1
N	2.54 ± 0.1
R	$0.5R \pm 0.05$

Package Dimension
TO-262
Unit :mm


DIM	MILLIMETERS
A	9.98 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	23.9 ± 0.3
h	3.1 ± 0.2
h1	9.16 ± 0.2
h2	13.2 ± 0.2
L	0.5 ± 0.1
11	1.3 ± 0.1
12	0.8 ± 0.1
N	2.45 ± 0.1

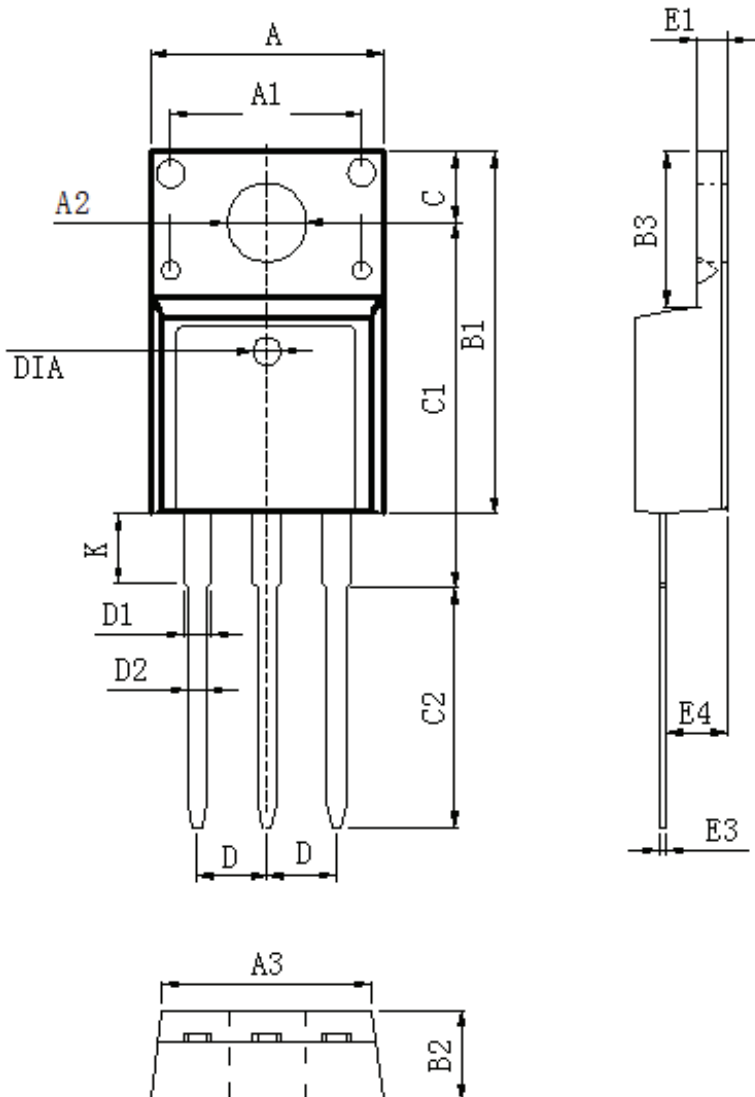
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Package Dimension

TO-220F

Unit :mm



DIM	MILLIMETERS
A	10.16 ± 0.3
A1	7.00 ± 0.1
A2	3.3 ± 0.2
A3	9.5 ± 0.2
B1	15.87 ± 0.3
B2	4.7 ± 0.2
B3	6.68 ± 0.4
C	3.3 ± 0.2
C1	12.57 ± 0.3
C2	10.02 ± 0.5
D	2.54 ± 0.05
D1	1.28 ± 0.2
D2	0.8 ± 0.1
K	3.1 ± 0.3
E1	2.54 ± 0.1
E3	0.5 ± 0.1
E4	2.76 ± 0.2
DIA	$\varnothing 1.5$ (deep 0.2)